



ELECTRIFY OUR WORLD™

Corporate Update Nov. '24
ir@navitassemi.com

GaNFast™

*World's First
GaN Power IC*

GeneSiC™

*World's Only Trench-Assisted
Planar SiC Technology*



DATA CENTER

MOBILE

ELECTRIC VEHICLES

10 YEARS



"Breaking Speed Limits with GaN Power ICs" APEC Keynote



Best Practices Award



World's First 20-Year Warranty



World's First GaN Sustainability Report
World's First 100,000 tons CO₂ Saved



GeneSiC Acquisition
Leading-Edge SiC



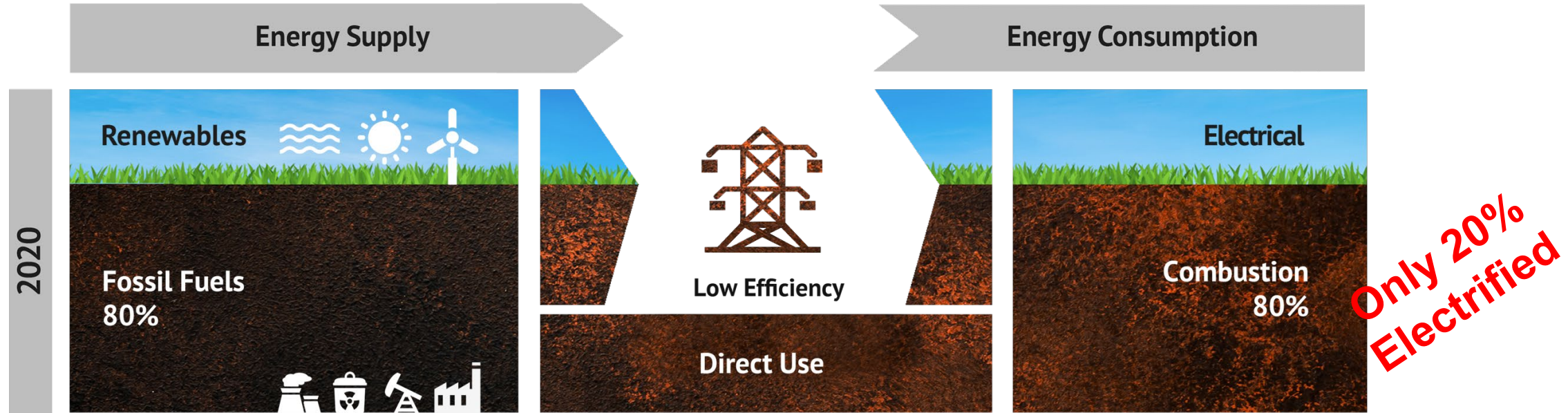
Fastest 75 Revenue Growth



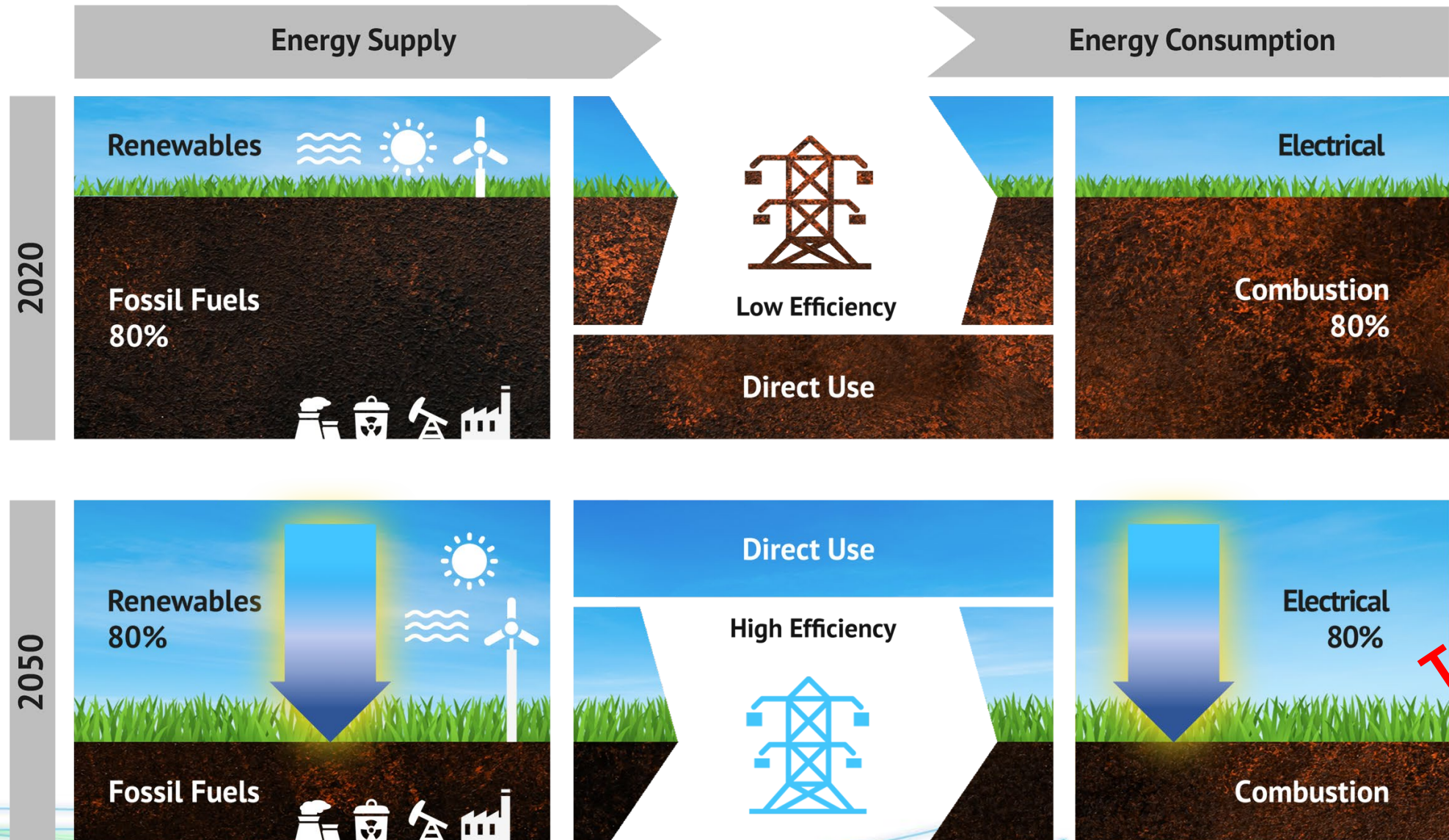
World's First Semi Company



The Fossil Fuel Challenge



The Electrified World



Target 80%



GaNFast™

GeneSiC™



Up to
20x
Faster
Switching⁽¹⁾

Up to
3x
Smaller &
Lighter⁽¹⁾

Up to
40%
Energy
Savings⁽¹⁾

Up to
3x
Higher
Power Density⁽¹⁾

Up to
3x
Faster
Charging⁽¹⁾

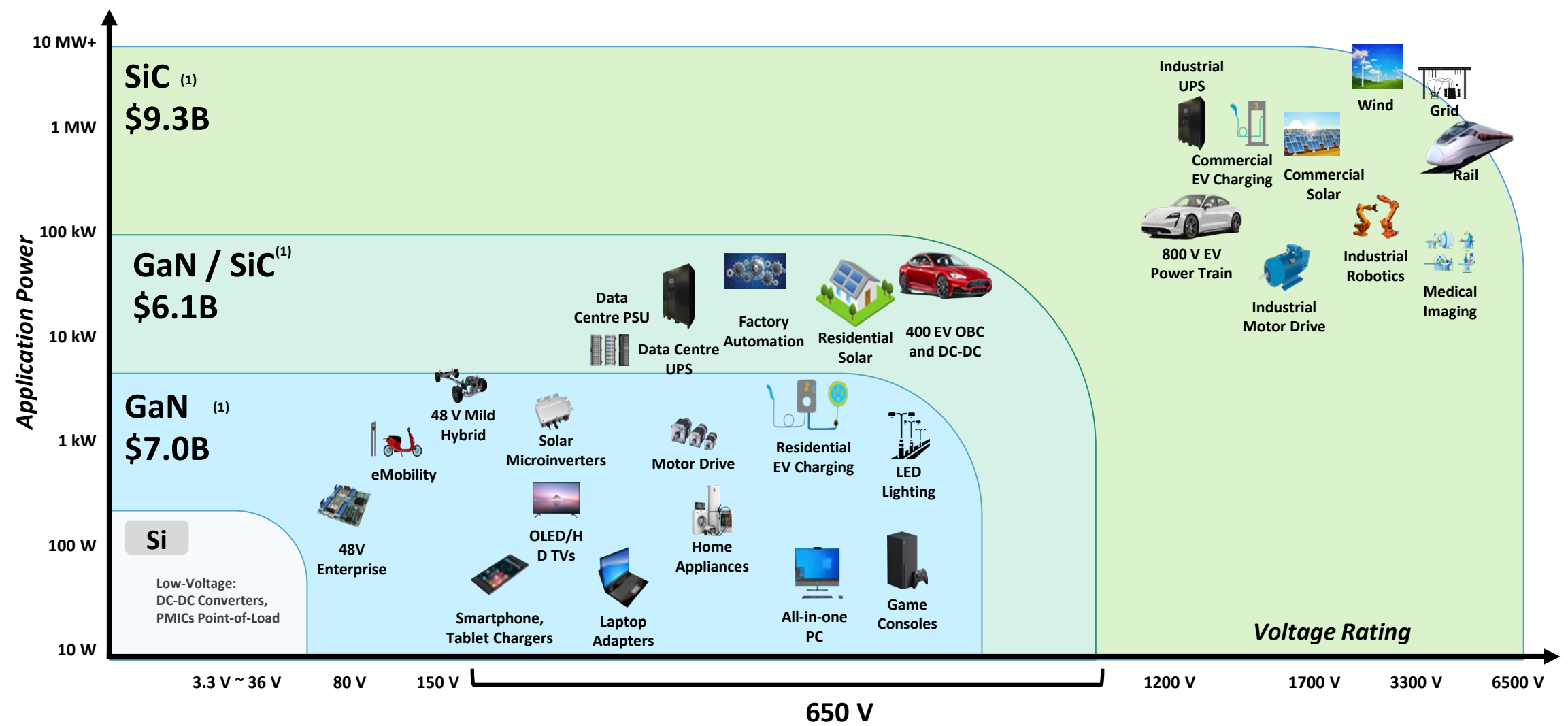
Up to
25%
Lower
System Cost⁽²⁾



GaN and SiC replacing Si in next-generation power applications

1. Statistical data is based on Navitas estimates of GaN-based systems compared to Si-based estimates in the 2024-2025 timeframe. Based on Navitas measurements of select GaN-based mobile wall chargers compared to Si-based chargers with similar output power, incl. 2019 study of 65W fast chargers, 2022 customer statement re 2.7 kW data center AC-DC
2. Navitas estimates based on customer feedback as the expected system cost saving overtime as of April 2023

\$22B+ GaN & SiC 'Pure-Play' Opportunity ⁽¹⁾



Notes: Axes not to scale
 1. Based on internal company estimates, Navitas believes that the potential market opportunity in 2026 is \$22B+ for GaN and SiC, replacing certain of the silicon market share
 2. Per Yole Development, 2024-2024 estimated market revenue



Key Patents in GaN and SiC

300+ Patents issued or pending encompassing key aspects of GaN power circuitry, analog and digital integration, and SiC device design and fabrication⁽¹⁾

Proprietary Design & Process

Led by pioneers in SiC and GaN, the Navitas team has a proprietary in-house Process Design Kit (PDK)

Rate of Innovation

Rapid design process and rate of commercialization create customer value and outpace competitors

New generation released every ~18 months

(1) Issued or pending

GaNFast Integration Drives Performance

Discrete Silicon

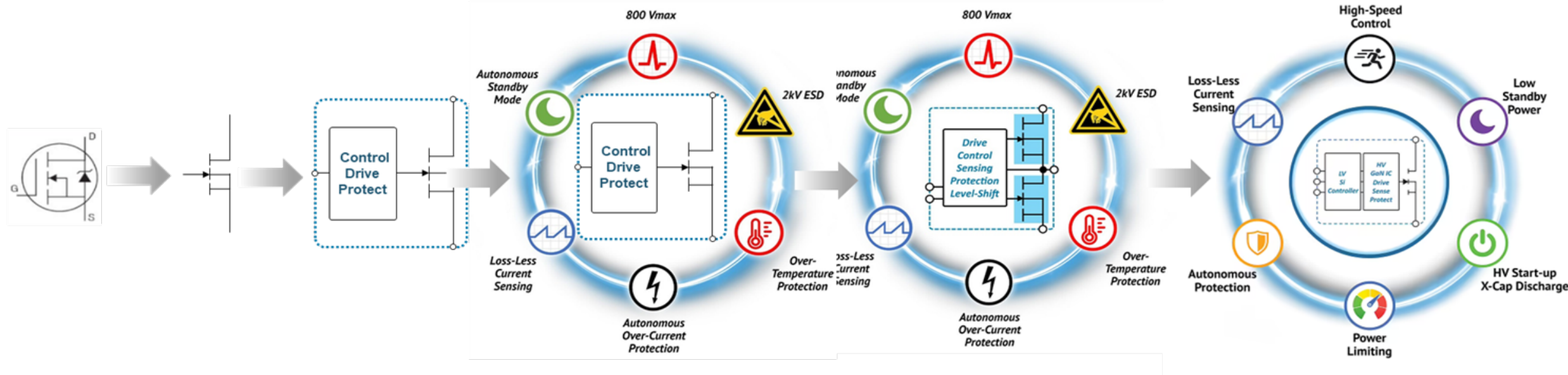
Discrete GaN

GaNFast™

GaNSense™

GaNSense Half-Bridge

GaNSense Control



- Old
- Slow
- Low efficiency

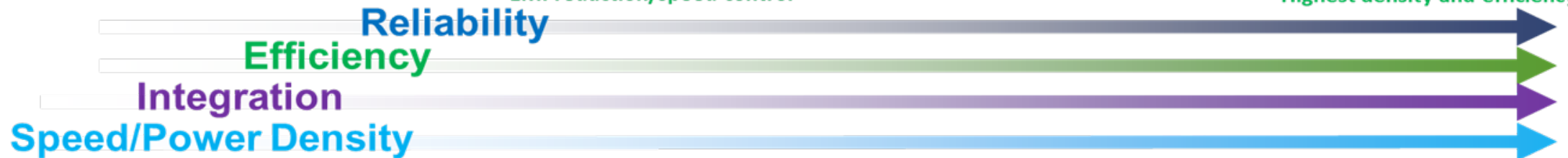
- Vulnerable input
- Difficult to use
- Sensitive to layout

- ✓ Robust input
- ✓ Easy to use
- ✓ Proven reliability

- GaNFast plus:*
- ✓ Autonomous protection
 - ✓ Loss-less current sensing
 - ✓ EMI reduction/speed control

- GaNSense plus:*
- ✓ Integrated HS, LS, level-shifted drive
 - ✓ Bootstrap power for high side
 - ✓ Complete protection

- GaNSense plus:*
- ✓ Integrated system controller
 - ✓ Fewest components
 - ✓ Highest density and efficiency



GaNSafe™

The World's Safest GaN

 Navitas



2 kV ESD



Easy EMI



High-Speed
Short-Circuit Protection



800 V
max



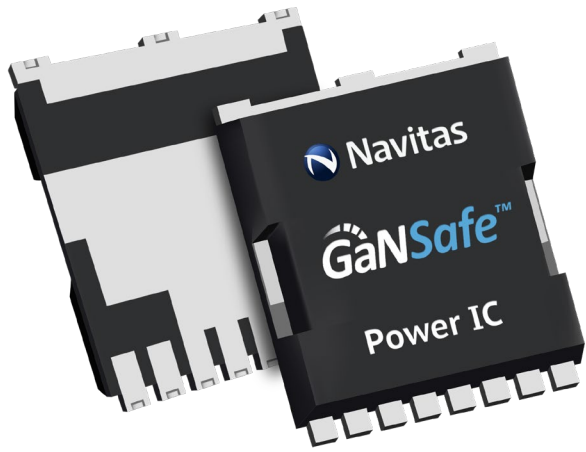
Robust
Operation



Easy Cooling



Industry's Only 20-Year Warranty



TOLL



TOLT

AI: Navitas Delivers The Power



Train GPT-MoE-1.8T in 90 Days

Blackwell GB200 NVL72
2000 GPUs | 4MW

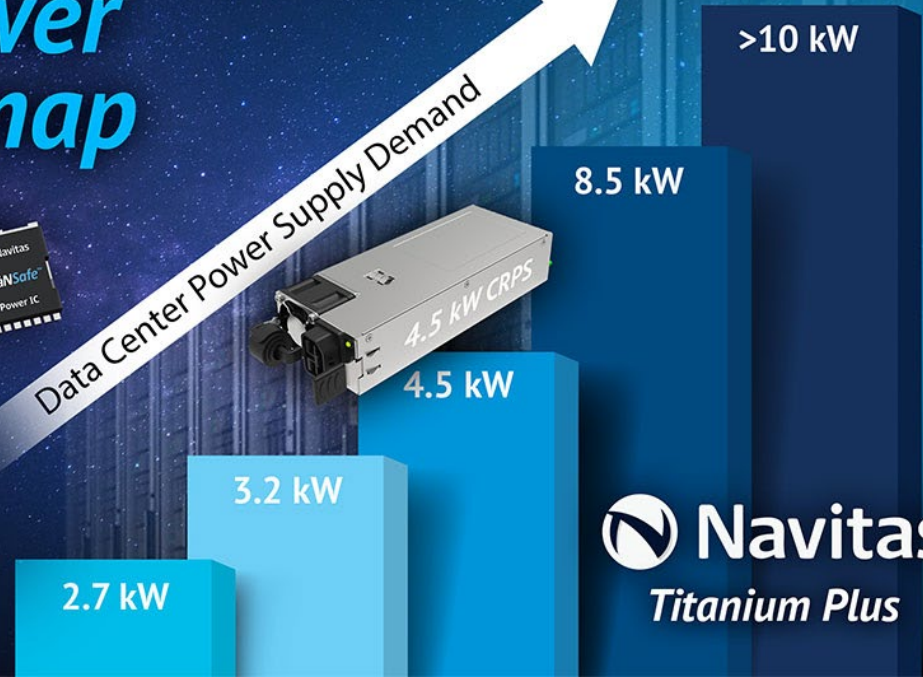
Up to 120 kW per rack



AI Power Roadmap



Data Center Power Supply Demand



- Power roadmap for **Hopper-Blackwell-Rubin** AI GPUs
- Power per-rack increasing from 30 to 480 kW
- Revenue ramping from Q3 2024
- 60 active customer developments

End Customer Targets



IntelliWeave

Phoenix, AZ
October 20-24th



 **Navitas**
Electrify Our World™

World's First 8.5 kW AI Data Center Power Supply Powered by GaN & SiC



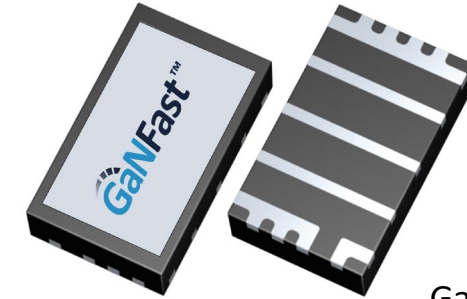
 **Navitas**
Electrify Our World™

- Intelliweave PFC digital control (patented)
 - Precision current-sharing, ultra-fast dynamic response and minimal phase error
 - Up to 30% energy savings (PFC): highest efficiency across load range, with 99.3% peak PFC efficiency
- Benchmark 8.5 kW, 3-phase AC-54V OCP & ORv3-compliant power
 - Optimized Gen-3 'Fast' SiC and GaNSafe™, 98% peak efficiency

OCP = Open Compute Project, ORv3 = Open Rack v3 industry standards

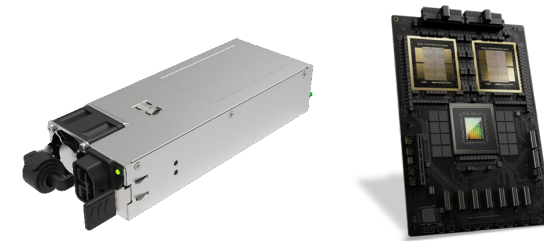
New MV GaNFast™ expands TAM by \$1B+

- Medium-voltage (MV) GaNFast™ range
 - 80-200V for 48V applications, 100s to 1,000s Watts
 - Samples expected Q4'24Q1'25, mass production target Q4'25
- Dual-sourcing arrangement with Infineon Technologies
 - Reciprocal access (cross-licensing) to GaN patent portfolios without concern for litigation
 - Trade secrets, 'know-how', innovations, 'go-to-market' and pricing strategies are independent
 - Expected to accelerate GaN adoption in mainstream applications by delivering reliable, advanced technology via reliable, parallel supply chains



GaNFast 80-200V
Dual-cool
3x5 mm QFN

- New applications (\$1B+ per year additional available market)
 - AI data centers
 - Secondary-side rectification in AC-48V 'silver-box' power supplies
 - Primary-side input to 48V-to-1.xV down-conversion to GPU/CPU/memory on the server board, via VRM/VRD



- EV
 - eScooters, eBikes, short-range city cars, etc.
 - Passenger and commercial upgrades (from 12/24V to 48V)



- AI-robotics
 - Land-based (vehicular, humanoid), and drones



GeneSiC™

Patented Trench-Assisted Planar SiC MOSFETs

Up to 6.5 kV

Largest range of SiC FETs & diodes
(650 V to 6.5 kV)



Fast Switching

Highest efficiency hard-switch, soft-switch
(Lowest E_{ON} , E_{OFF} , E_{ZVS} losses)

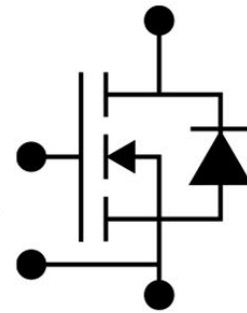


Cool Operation

Lowest $R_{DS(ON)}$ at high temperature
(25% lower than industry typical)



Cool.
Fast.
Rugged.



Long Short-Circuit Withstand Time

World-class survival duration
in fault condition



High-Power Paralleling

Matching currents
(Stable V_{TH})



100%-Tested Robust Avalanche

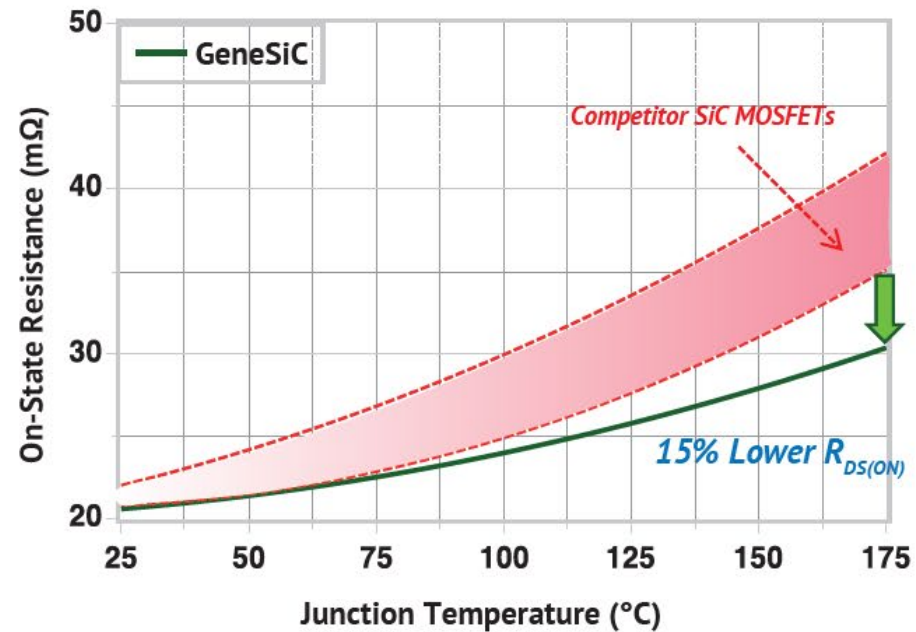
Highest published capability to handle
excess energy in fault condition



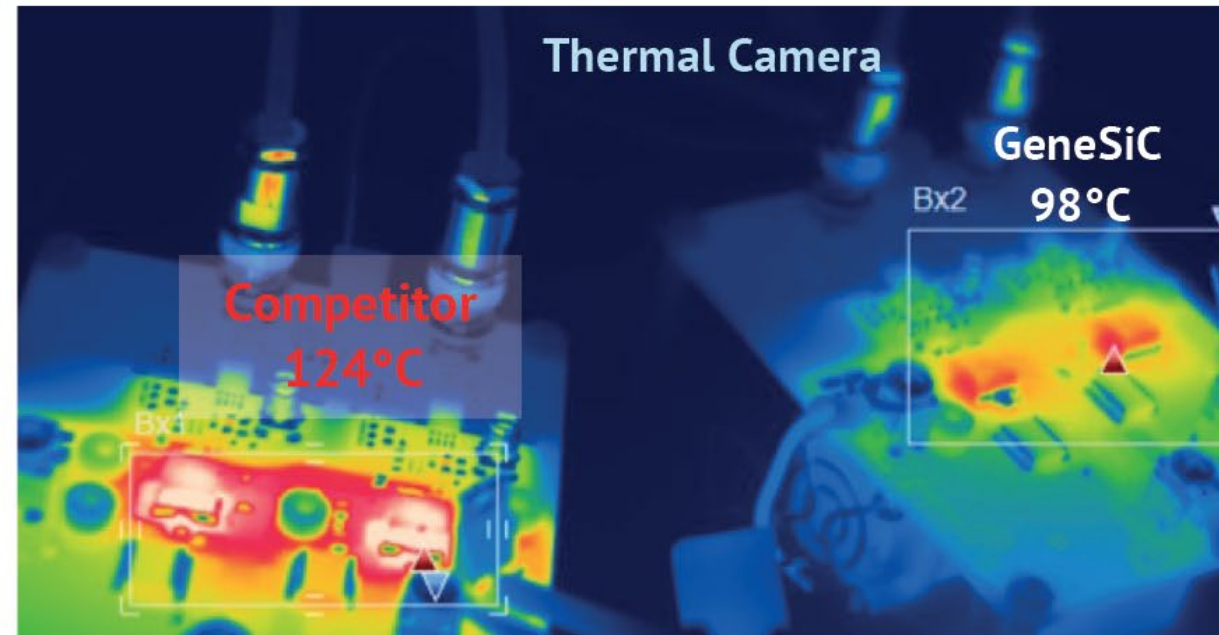
Best of Both: Trench-Assisted Planar Gate

	<p>SiC Planar</p>	<p>SiC Trench</p>	<p>GeneSiC</p>
Manufacturability	<ul style="list-style-type: none"> • Repeatable • High Yield • Low Cost 	<ul style="list-style-type: none"> • Complex manufacturing • Lower Yield • High Cost 	<ul style="list-style-type: none"> • Repeatable • High Yield • Low Cost
Performance	<ul style="list-style-type: none"> • Higher On-Resistance/area • Slow switching • High On-Resistance increase with temp 	<ul style="list-style-type: none"> • Lower On-Resistance / area than Planar • Faster switching • Very High On-Resistance increase with temp 	<ul style="list-style-type: none"> • Lowest On-Resistance / area • Fastest switching • Lowest On-Resistance increase with temp
Reliability	<ul style="list-style-type: none"> • Rugged due to Planar gate 	<ul style="list-style-type: none"> • Lower gate reliability due to defective trench sidewall in SiC 	<ul style="list-style-type: none"> • Rugged due to Planar gate • Highest 100% tested avalanche ratings

$$R_{DS(ON)} \text{ vs } T_j$$



In-Circuit, High-Speed Test



- **GeneSiC vs. competitor SiC FET**

- » 1200 V, 20 mΩ, TO-247-4L
- » Higher drain current
- » Lower conduction losses
- » Cooler operation

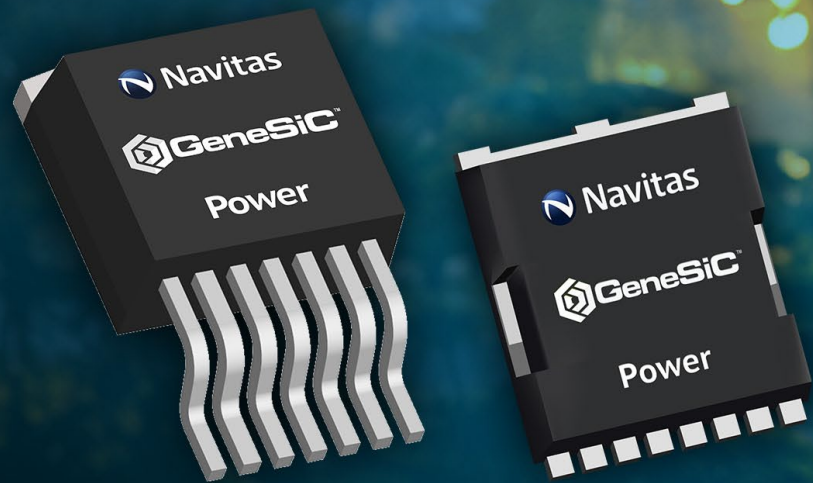
- **GeneSiC vs. competitor SiC FET**

- » 1200 V, 40 mΩ, D2pak in half-bridge
- » 150 kHz switching = ~10x faster than Si IGBT
- » 30% lower FET loss vs. other SiC
- » 25°C cooler operation = 3x longer lifetime

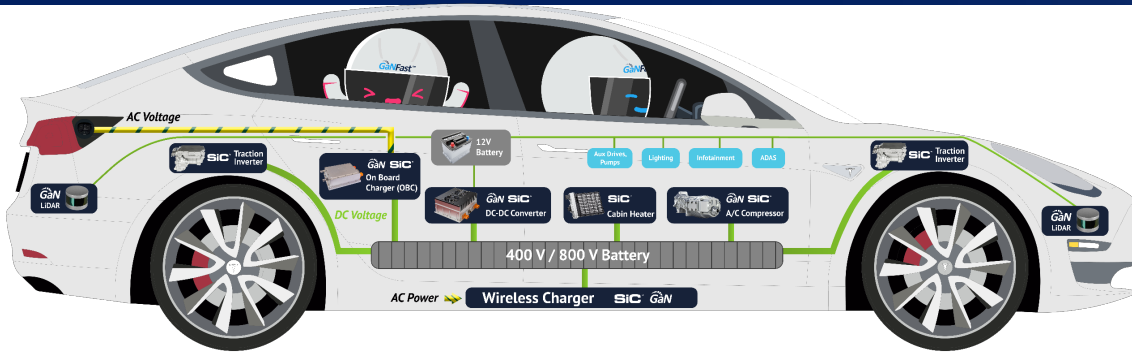
Gen-3 'Fast' SiC MOSFETs

Automotive Qualified

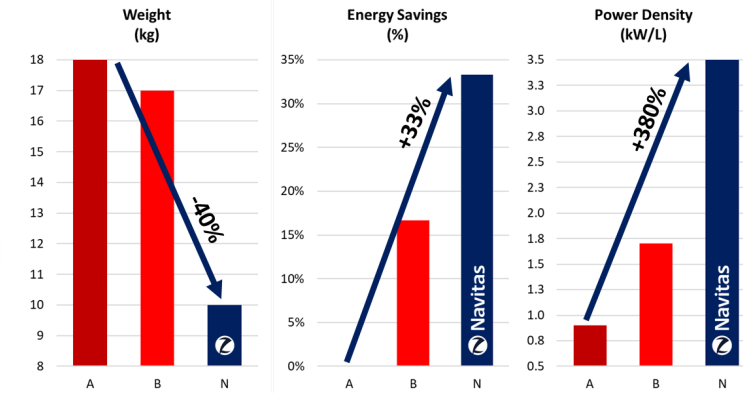
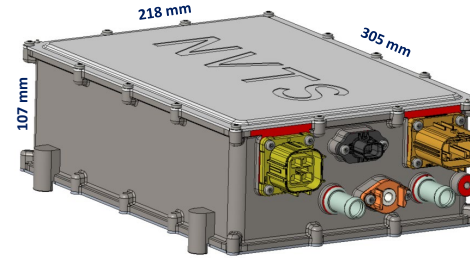
AEC-Q101



EV: Customer Pipeline +25% to 200+ Projects

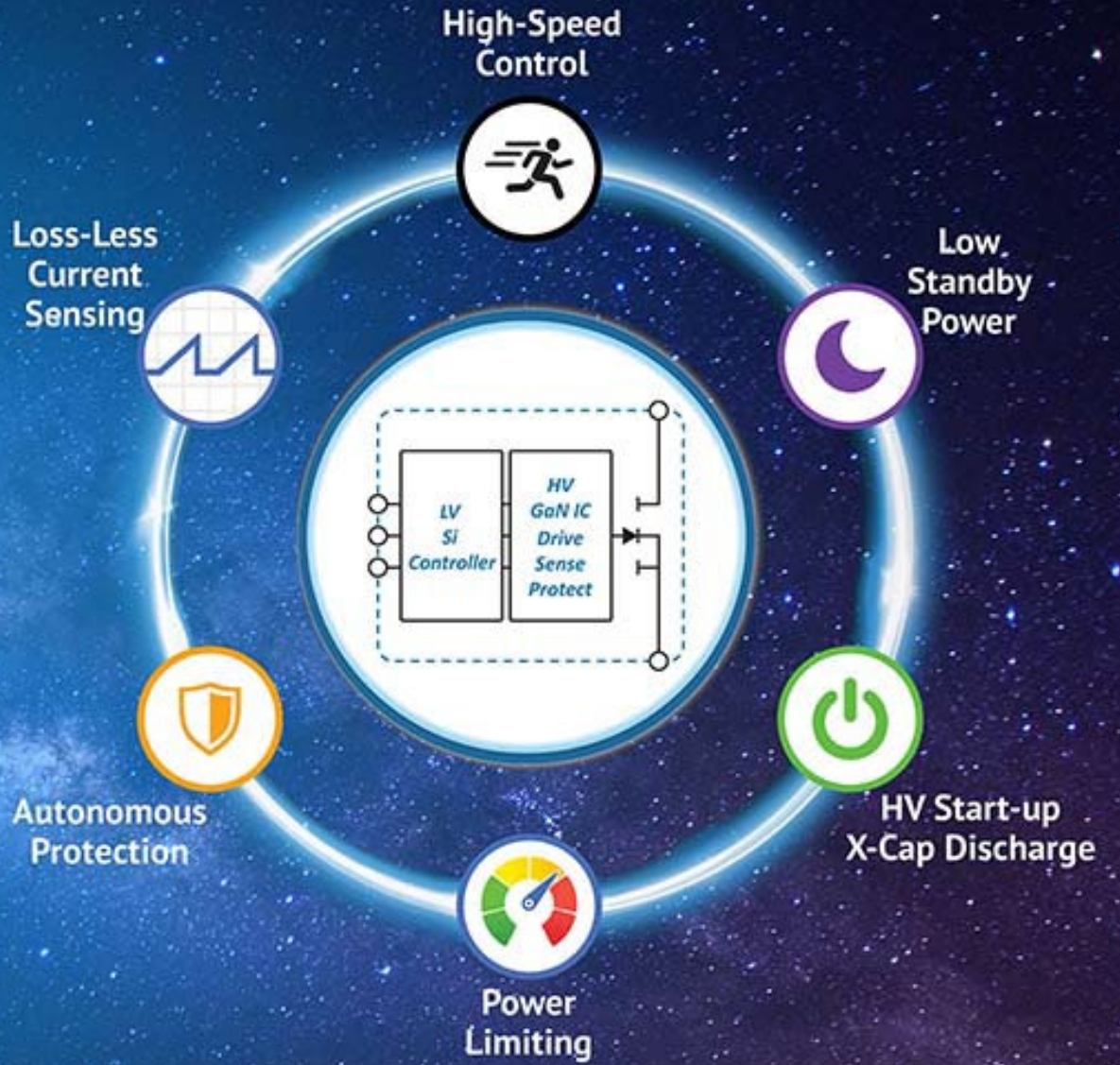


22 kW, OBC 3-in-1



- 400V and 800V battery solutions; GaN + SiC
- Up to 3x smaller, 40% lighter, 30% energy savings
- 200+ customer projects in development
- 6 new design wins in Q3





 **Navitas**

GaNSlim™



*Simple
Fast
Integrated*



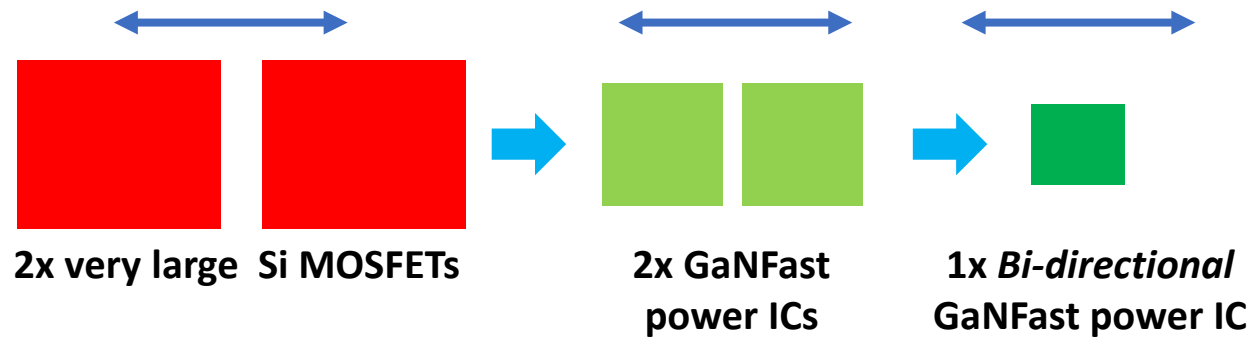
Navitas
Electrify Our World™

Mobile: GaN Goes Mainstream

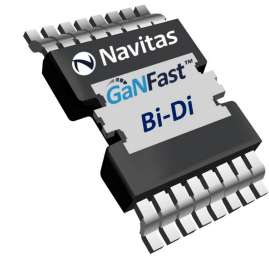
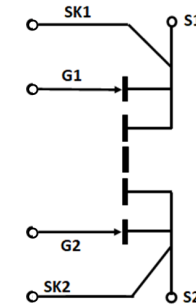
- Xiaomi, OPPO “30% GaN in 2024”; Samsung expand from Galaxy S to Galaxy A, +Fold, + Flip
- Three new Tier-1 OEM wins start ramp Q2 ‘25
- GaNSlim with 26 new wins in Q3



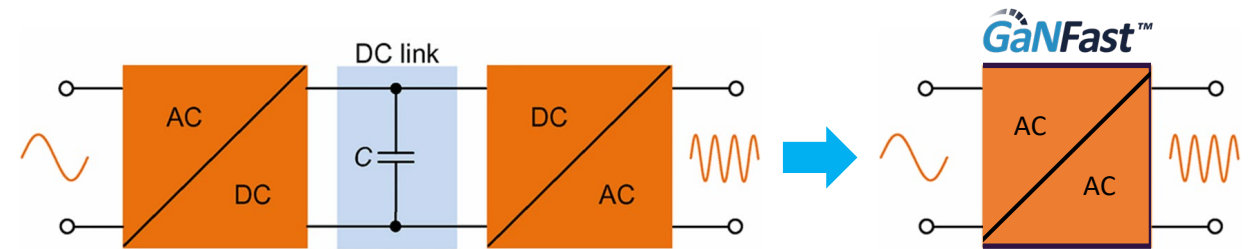
World's First Bi-Directional GaN Power IC



Up to 9x smaller die



- For bi-directional operation, traditional power semis need many, large devices
- Proprietary, 'bi-directional' GaNFast power ICs:
 - Smallest, most efficient, lowest system cost solution
 - Optimized for fast switching, AC voltage applications
 - Enable 'previously-impractical' topologies
 - Integrated circuitry ensures reliability



Direct power conversion with bi-directional GaNFast means simple, small, efficient, low system-cost AC-AC conversion

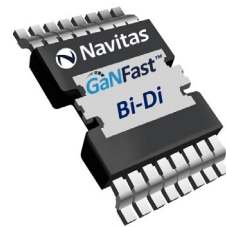
- Applications:
 - High-power industrial, solar, energy storage, motor drives
- Topologies:
 - Heric Inverter, Vienna Converter, T-type NPC Inverter, Matrix AC/AC Converter

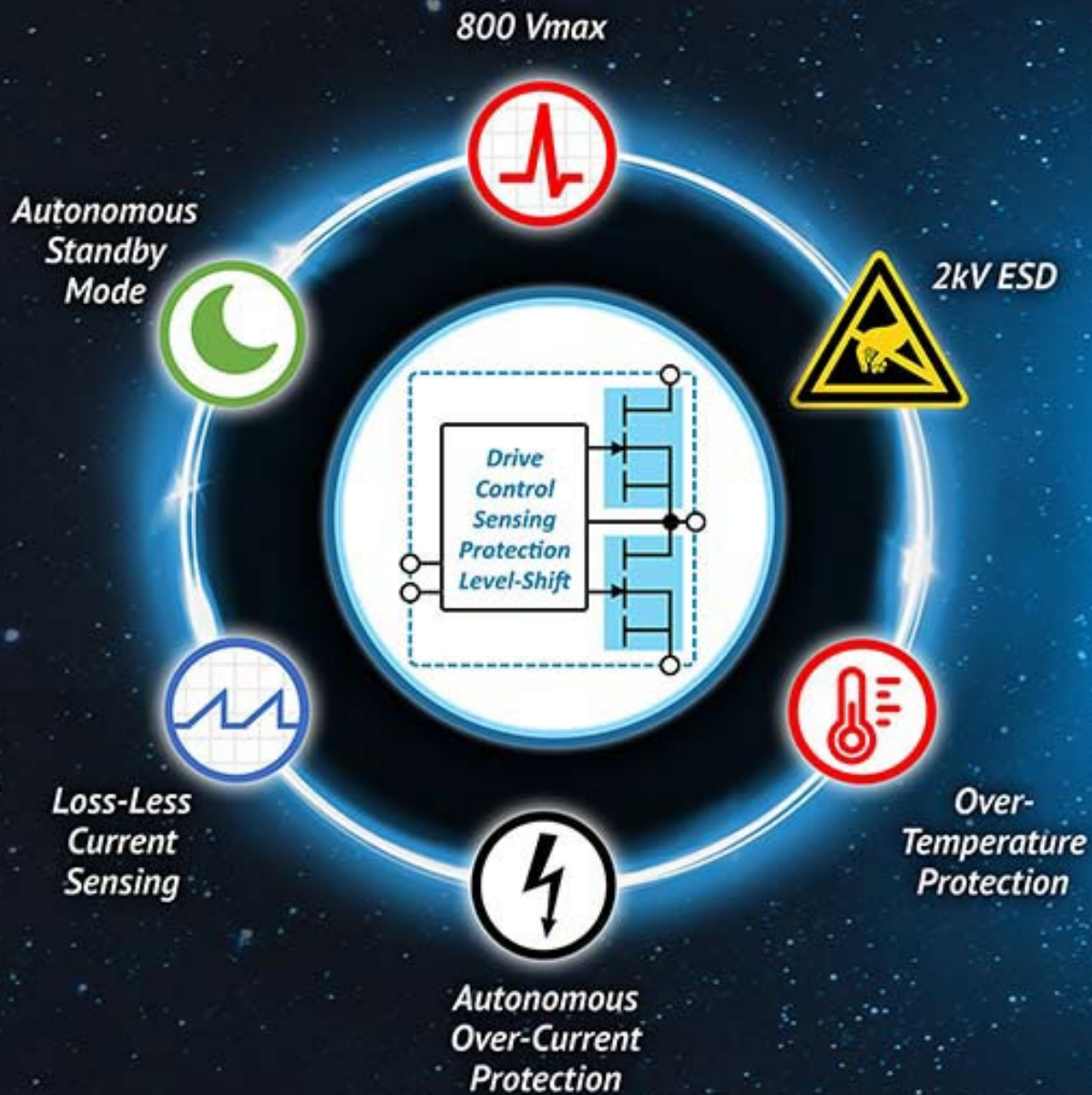
GaNFast™
Vienna
Rectifier



Solar / Storage: First GaN Micro-inverters

- 100+ customer projects in development
 - GaN for residential micro-inverters
 - SiC for higher-power, higher-voltage string inverters
 - SiC for energy storage systems
- Majority of top-10 string inverter OEMs engaged or in production
- Major US GaN micro-inverter mid '25
- 10 new customers wins in Q3 '24
- Best-in-class SiC, GaN, new bi-directional GaN
- Smaller, lighter, lower system cost



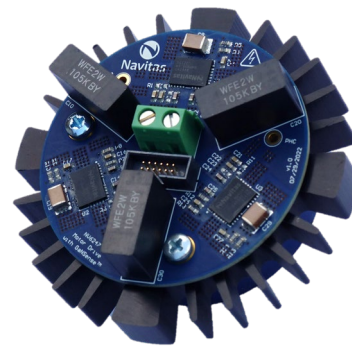


Appliance & Industrial: Growing Pipeline for 2025-26 Ramp Navitas

- Diverse GaN & SiC portfolio for a diverse market
- Diverse customers, regions, applications:
 - 7 / top 10 appliance leaders
 - Motors, pumps, air-con, heat pumps, compressors, chargers, fans, conveyors, robots, auxiliary supplies...
- 25 new projects wins expected to ramp production in 2025/26

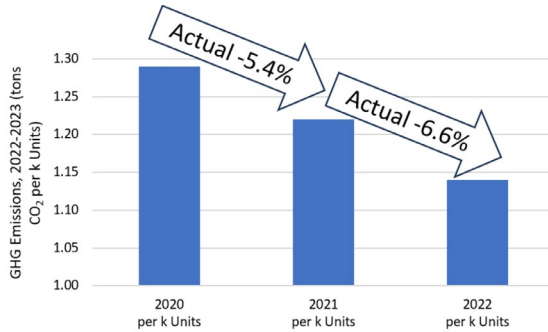


- 300 W, 3-phase motor drive
- 3x NV6247 GaNSense Half-bridges
- 100 kHz, high density, strong protection
- Peak temp only **52°C, with No Heatsink**

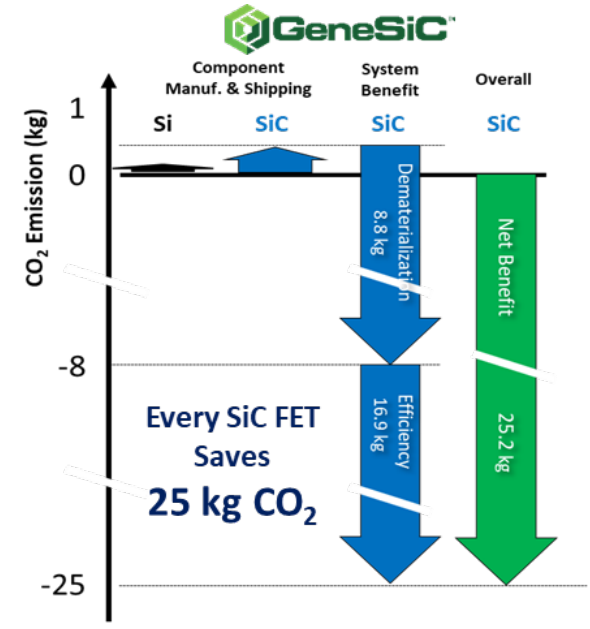
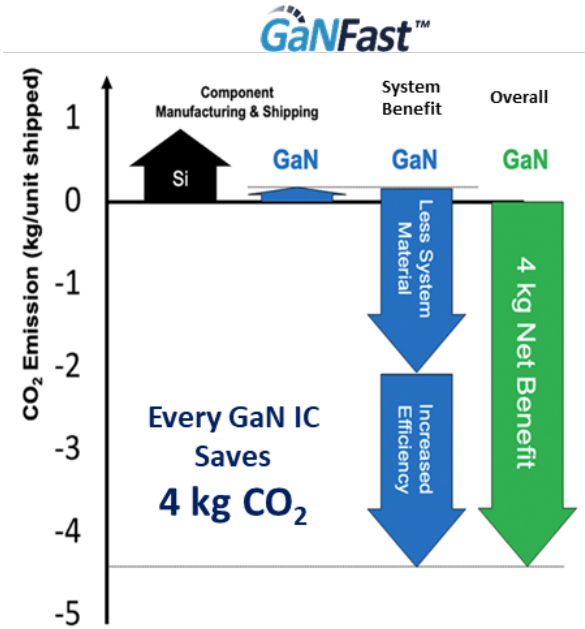
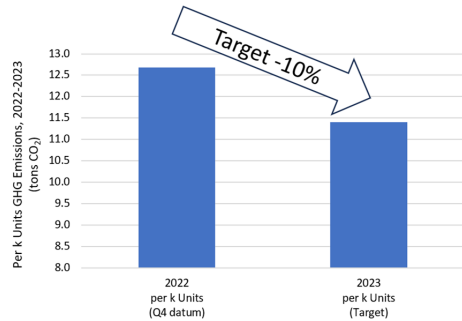


Accelerating Sustainability

Navitas Corporate GHG Scope 2, 3 (GaN only)



Navitas Corporate GHG Scope 2, 3 (GaN + SiC)



Feb '22 World's first GaN Sustainability Report



May '22 World's first semiconductor Company certified CarbonNeutral®



Aug '22 First 100,000 tons CO₂ saved [Nov'23 over 200,000 tons]

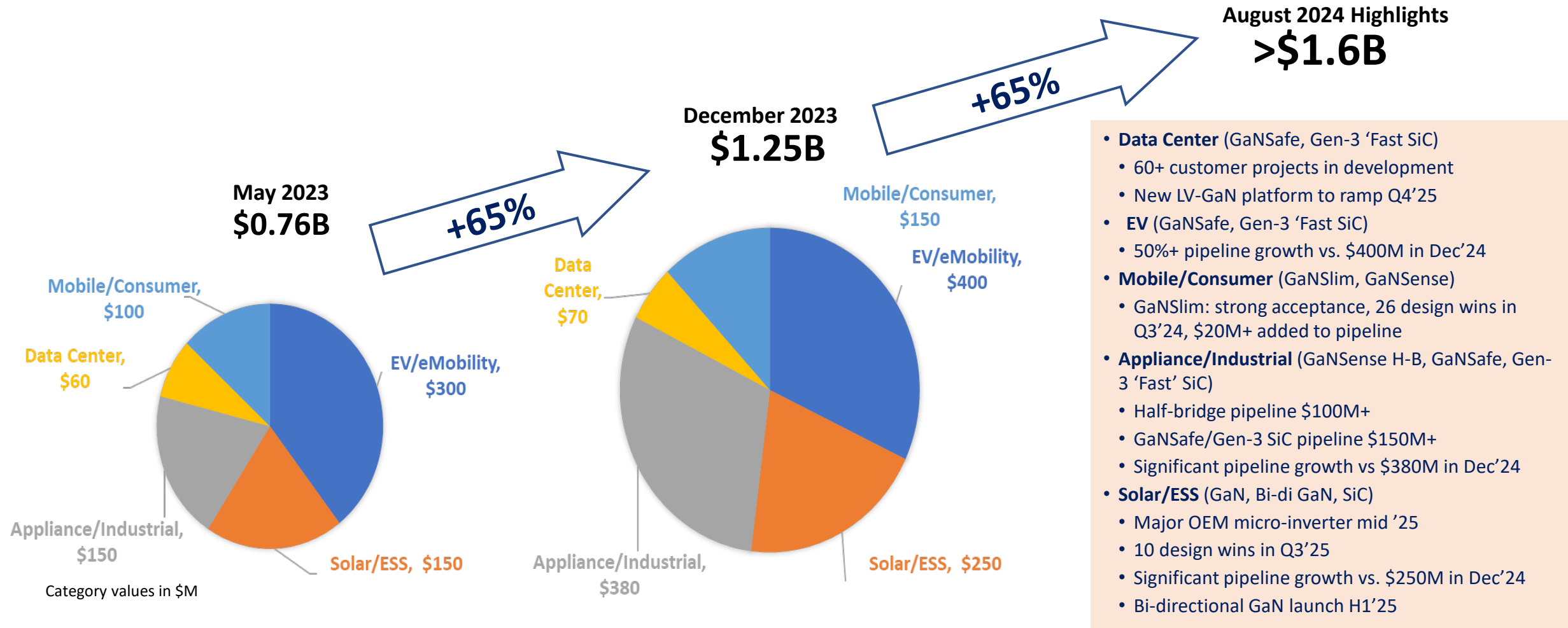


Oct '22 Recognized as Industry-Leading Sustainability Company



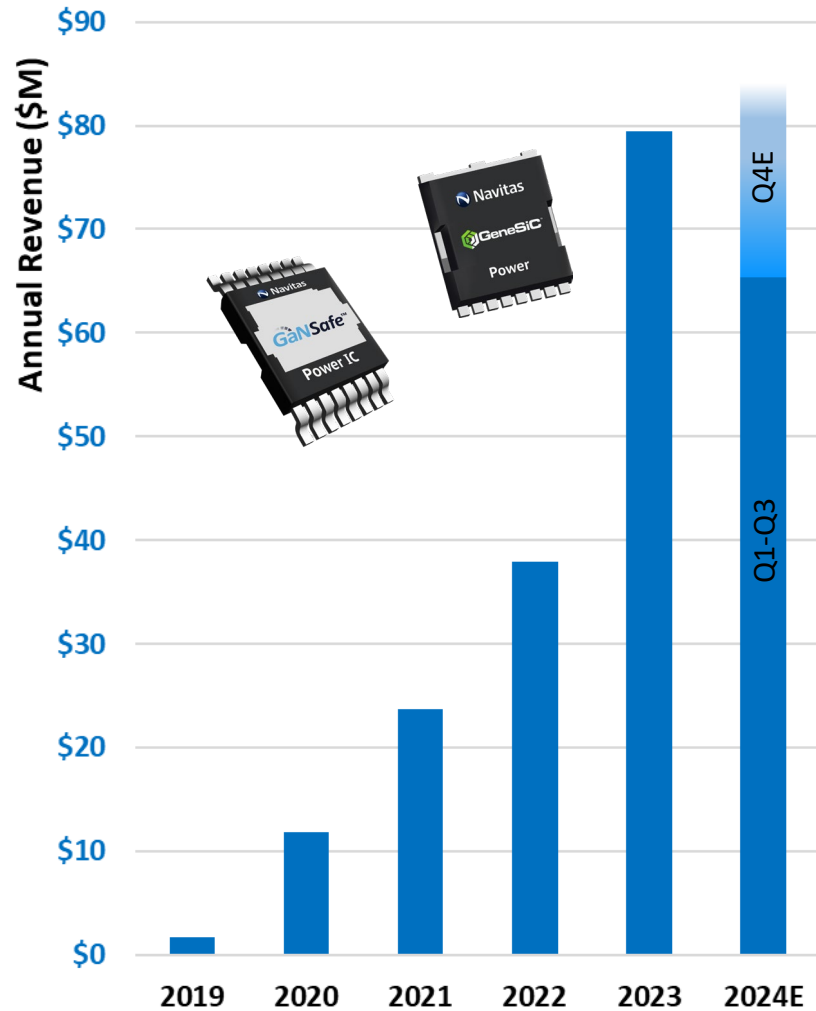
Nov '23 Consolidated GaN + SiC Sustainability Report

Customer Pipeline⁽¹⁾ Over \$1.6B



(1) Committed production programs, lifetime revenue, verified technical fit, value proposition and high interest in Navitas solution. Existing mass-production wins excluded. Start dates 'near-term' per market, life-cycle per market, second sourcing accounted for as appropriate.

Navitas: Growing Faster than the Market



- Q3 2024 Financial Report (November 5th, 2024)
 - Q3'24 Revenue \$21.7M (up 22% YTD vs '23)
 - Cash ~\$100M, no debt
 - ~187M shares outstanding
 - Customer pipeline >>\$1.6B
 - Good position to scale to long-term growth and profitability

“Our leading-edge technology is fueling robust customer pipeline growth in each end market, led by AI data centers with multiple customers ramping production with our GaN *and* SiC-based power systems.”

- Gene Sheridan, CEO and co-founder.

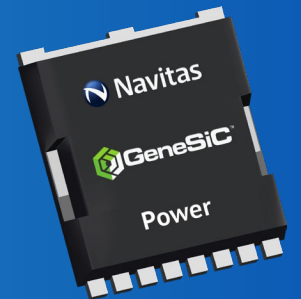


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